

D6-8-650-7-P



Application

Particle Sensor
Industrial Optical Sensor

Property

Wavelength $\lambda = 650 \text{ nm}$
Output Power = 7 mW
Package Type = $\varnothing 5.6\text{mm}$

Introduction

Egismos currently markets AlGaInP based red laser diodes in the 635nm~ 670nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer. Egismos laser diodes are highly rated in a broad range of applications .

Laser Diode Key features

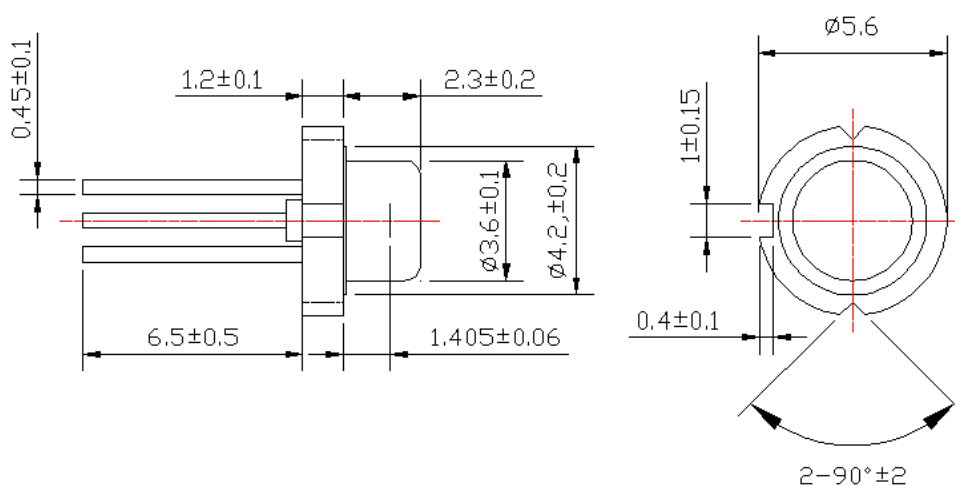
Absolute Maximum Rating at $T_c=25^\circ\text{C}$

Items		Symbols	Values	Unit
Operating Current power		P_o	7	mW
Reverse Voltage	LD	V_R	2	V
Operating Temperature		T_{case}	-40~+85	$^\circ\text{C}$
Storage Temperature		T_s	-40~+90	$^\circ\text{C}$

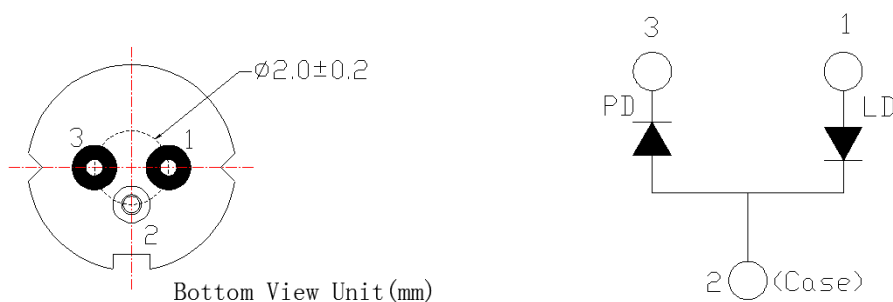
Electrical and Optical Characteristics at Tc=25°C

Item	Symbols	Min	Typ.	Max.	Unit	Condition
Threshold Current	I_{th}	-	15	25	mA	-
Operating Current	I_{op}	-	22	30	mA	Po=7mW
Operating Voltage	V_{op}	-	2.2	2.4	V	Po=7mW
Peak Wavelength	λ_p	645	658	666	nm	Po=7mW
Beam Divergence (FWHM)	θ_f	5	8	12	deg	Po=7mW
Beam Divergence (FWHM)	θ_{\pm}	22	26	30	deg	Po=7mW
Monitor Current	I_m	0.1	0.2	0.4	mA	Po=7mW

Package Drawing



Electrical connection



Specifications are subject to change without notice.

